

H5N3008P

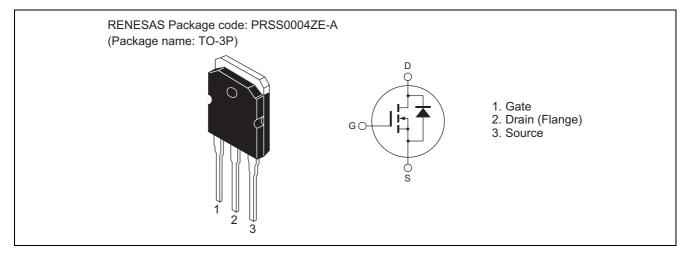
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G0539-0300 Rev.3.00 Oct 16, 2006

Features

- Low on-resistance
- Low leakage current
- www.DataSheet4U.High speed switching
 - Built-in fast recovery diode

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	300	V
Gate to Source voltage	V _{GSS}	±30	V
Drain current	ID	40	A
Drain peak current	Note1 I _{D (pulse)}	160	A
Body-Drain diode reverse Drain current	I _{DR}	40	A
Avalanche current	I _{AP} ^{Note3}	30	A
Channel dissipation	Pch ^{Note2}	150	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C



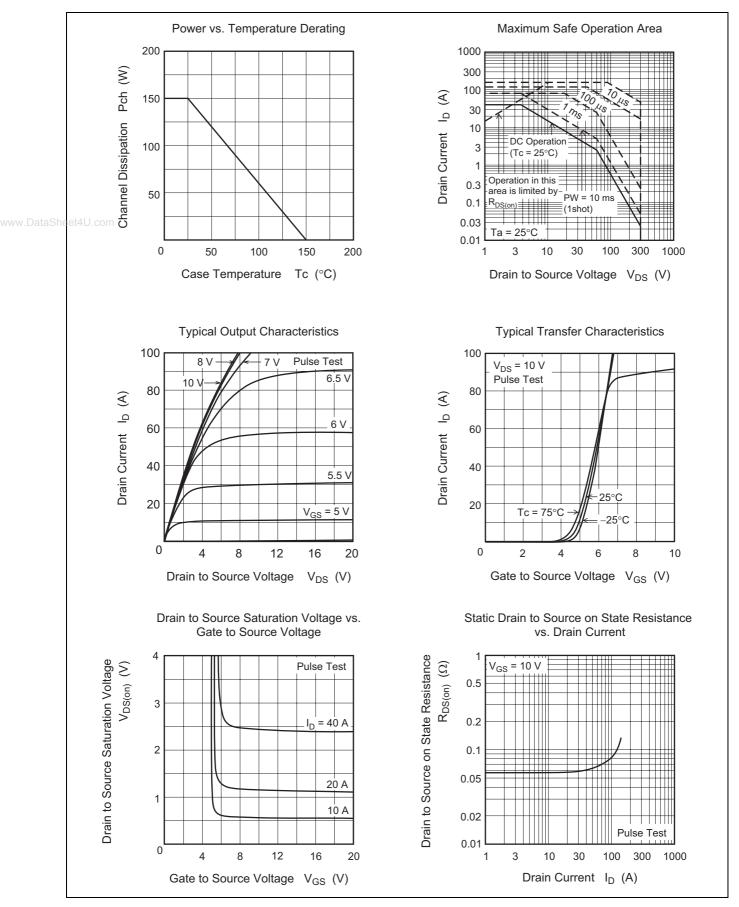
Electrical Characteristics

Symbol	Min	Тур	Max	Unit	Test conditions	
V _{(BR)DSS}	300	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
I _{DSS}	_	—	10	μΑ	$V_{DS} = 300 \text{ V}, V_{GS} = 0$	
I _{GSS}	_	—	±0.1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$	
V _{GS(off)}	2.0	—	4.0	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	
yfs	19	32	—	S	$I_D = 20 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$	
R _{DS(on)}	_	0.058	0.069	Ω	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$	
Ciss	_	5150	—	pF	V _{DS} = 25 V	
Coss	_	590	—	pF	V _{GS} = 0 f = 1 MHz	
Crss	-	90	_	pF		
t _{d(on)}	_	60	—	ns	$ I_D = 20 \text{ A} \\ V_{GS} = 10 \text{ V} \\ R_L = 7.5 \Omega \\ Rg = 10 \Omega $	
tr	_	170	—	ns		
t _{d(off)}	_	210	—	ns		
t _f	_	140	—	ns		
Qg	_	130	—	nC	$V_{DD} = 240 V$ $V_{GS} = 10 V$ $I_D = 40 A$	
Qgs	_	25	—	nC		
Qgd	_	60	—	nC		
V _{DF}	_	1.0	1.5	V	$I_F = 40 \text{ A}, V_{GS} = 0^{Note4}$	
trr		170	_	ns	$I_F = 40 \text{ A}, V_{GS} = 0$	
Qrr	_	1.1	—	μC	diF/dt = 100 A/μs	
	V(BR)DSS IDSS IGSS VGS(off) Jyfs] RDS(on) Ciss Coss Crss td(on) tr Qg Qgs Qgd VDF trr	V _{(BR)DSS} 300 I _{DSS} I _{GSS} V _{GS(off)} 2.0 Jyfs 19 R _{DS(on)} Ciss Coss Crss t _{d(on)} t _{d(off)} t _f Qg Qgs Qgd V _{DF} trr	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	

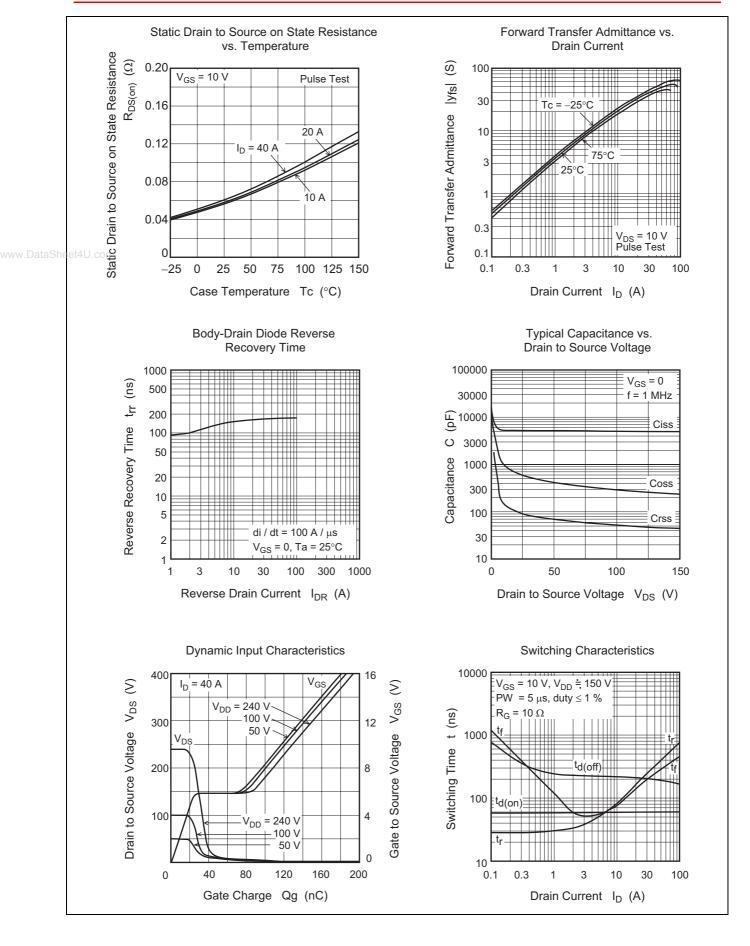
Notes: 4. Pulse test



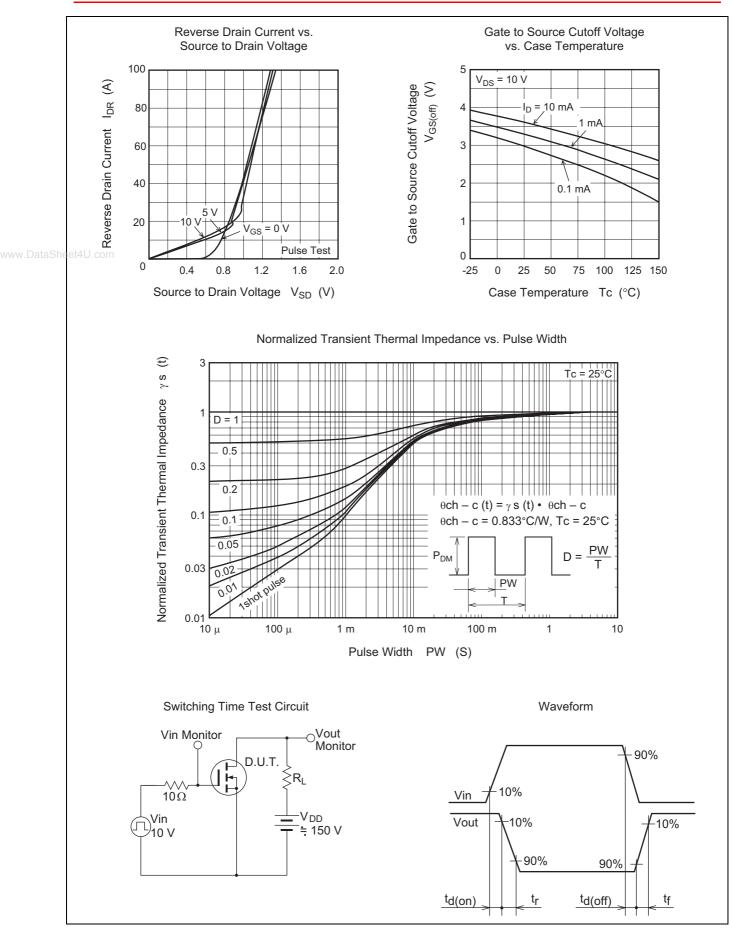
Main Characteristics





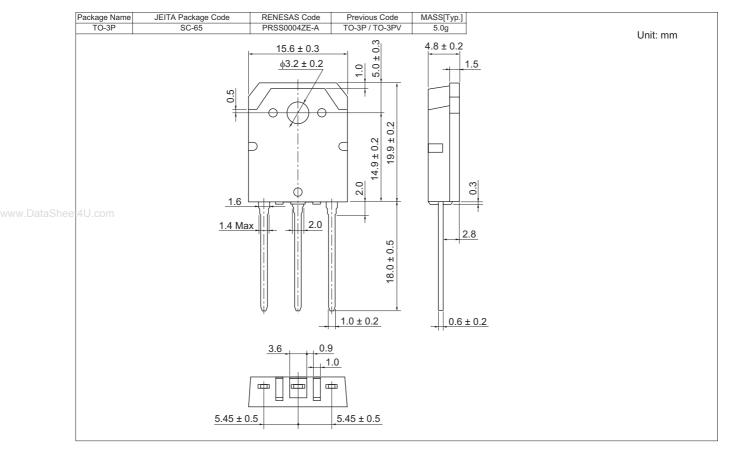








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N3008P-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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